
HB56UW3273 Series

33554432-word $\times$ 72-bit High Density Dynamic RAM Module

HITACHI

ADE-203-653 (Z)
Preliminary
Rev. 0.0
Sep. 6, 1996

Description

The HB56UW3273 Series belongs to 8-byte DIMM (Dual in-line Memory Module) family, and has been developed an optimized main memory solution for 4 and 8-byte processor applications. The HB56UW3273E Series is a 32 M $\times$ 72 Dynamic RAM Module, mounted 36 pieces of 64-Mbit DRAM (HM5165405ATT) sealed in TSOP package and 2 pieces of 16-bit BiCMOS line driver (74LVT16244) sealed in TSSOP package. The HB56UW3273EJ Series is a 32 M $\times$ 72 Dynamic RAM Module, mounted 36 pieces of 64-Mbit DRAM (HM5165405AJ) sealed in SOJ package and 2 pieces of 16-bit BiCMOS line driver (74LVT16244) sealed in TSSOP package. The HB56UW3273 Series offers Extended Data Out (EDO) Page Mode as a high $\bar{A}$ $\bar{i}$ $\bar{i}$ speed access mode. An outline of the HB56UW3273 Series is 168-pin socket type package (dual lead out). Therefore, the HB56UW3273 Series makes high density mounting possible without surface mount technology. The HB56UW3273 Series provides common data inputs and outputs. Decoupling capacitors are mounted beside each TSOP or SOJ on the its module board.

Features

- 168-pin socket type package (Dual lead out)
 - Outline : 133.35 mm (Length) $\times$ 60.96 mm (Height) $\times$ 4.00 mm (Thickness) (HB56UW3273E Series)
Outline : 176.53 (133.35) mm (Length) $\times$ 41.91 mm (Height) $\times$ 9.00 mm (Thickness) (HB56UW3273EJ Series)
 - Lead pitch : 1.27 mm
- Single 3.3 V supply (± 0.3 V)
- High speed
 - Access time: $t_{RAC} = 60$ ns/70 ns (max)
 - Access time: $t_{CAC} = 20$ ns/23 ns (max)
- Low power dissipation
 - Active mode: 12.02 W/10.73 W (max)
 - Standby mode (TTL): 295.2 mW (max)
- JEDEC standard outline buffered 8-byte DIMM

Preliminary: This document contains information on a new product. Specifications and information contained herein are subject to change without notice.

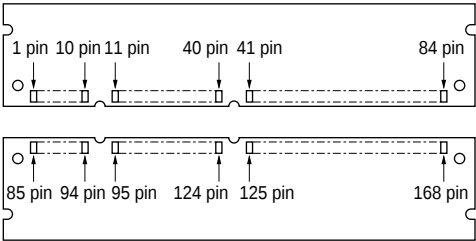
HB56UW3273 Series

- Buffered input except $\overline{\text{RAS}}$ and DQ
- 4-byte interleave enabled, dual address input (A0/B0)
- EDO page mode capability
- 4096 refresh cycles: 64 ms
- 2 variations of refresh
 - $\overline{\text{RAS}}$ -only refresh
 - $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh
- TTL compatible

Ordering Information

Type No.	Access time	Package	Contact pad
HB56UW3273E-6A	60 ns	168-pin dual lead out socket type	Gold
HB56UW3273E-7A	70 ns		
HB56UW3273EJ-6A	60 ns		
HB56UW3273EJ-7A	70 ns		

Pin Arrangement



Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name
1	V_{SS}	43	V_{SS}	85	V_{SS}	127	V_{SS}
2	DQ0	44	$\overline{\text{OE}}2$	86	DQ36	128	NC
3	DQ1	45	$\overline{\text{RE}}2$	87	DQ37	129	$\overline{\text{RE}}3$
4	DQ2	46	$\overline{\text{CE}}4$	88	DQ38	130	$\overline{\text{CE}}5$
5	DQ3	47	NC	89	DQ39	131	NC
6	V_{CC}	48	$\overline{\text{WE}}2$	90	V_{CC}	132	$\overline{\text{PDE}}$
7	DQ4	49	V_{CC}	91	DQ40	133	V_{CC}
8	DQ5	50	NC	92	DQ41	134	NC
9	DQ6	51	NC	93	DQ42	135	NC
10	DQ7	52	DQ18	94	DQ43	136	DQ54

Pin Arrangement (cont)

Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name
11	DQ8	53	DQ19	95	DQ44	137	DQ55
12	V _{SS}	54	V _{SS}	96	V _{SS}	138	V _{SS}
13	DQ9	55	DQ20	97	DQ45	139	DQ56
14	DQ10	56	DQ21	98	DQ46	140	DQ57
15	DQ11	57	DQ22	99	DQ47	141	DQ58
16	DQ12	58	DQ23	100	DQ48	142	DQ59
17	DQ13	59	V _{CC}	101	DQ49	143	V _{CC}
18	V _{CC}	60	DQ24	102	V _{CC}	144	DQ60
19	DQ14	61	NC	103	DQ50	145	NC
20	DQ15	62	NC	104	DQ51	146	NC
21	DQ16	63	NC	105	DQ52	147	NC
22	DQ17	64	NC	106	DQ53	148	NC
23	V _{SS}	65	DQ25	107	V _{SS}	149	DQ61
24	NC	66	DQ26	108	NC	150	DQ62
25	NC	67	DQ27	109	NC	151	DQ63
26	V _{CC}	68	V _{SS}	110	V _{CC}	152	V _{SS}
27	$\overline{WE}0$	69	DQ28	111	NC	153	DQ64
28	$\overline{CE}0$	70	DQ29	112	$\overline{CE}1$	154	DQ65
29	NC	71	DQ30	113	NC	155	DQ66
30	$\overline{RE}0$	72	DQ31	114	$\overline{RE}1$	156	DQ67
31	$\overline{OE}0$	73	V _{CC}	115	NC	157	V _{CC}
32	V _{SS}	74	DQ32	116	V _{SS}	158	DQ68
33	A0	75	DQ33	117	A1	159	DQ69
34	A2	76	DQ34	118	A3	160	DQ70
35	A4	77	DQ35	119	A5	161	DQ71
36	A6	78	V _{SS}	120	A7	162	V _{SS}
37	A8	79	PD1	121	A9	163	PD2
38	A10	80	PD3	122	A11	164	PD4
39	NC	81	PD5	123	NC	165	PD6
40	V _{CC}	82	PD7	124	V _{CC}	166	PD8
41	NC	83	ID0 (V _{SS})	125	NC	167	ID1 (V _{SS})
42	NC	84	V _{CC}	126	B0	168	V _{CC}

Pin Description

Pin name	Function
A0 to A11, B0	Address input — Row address (D0 to D35) A0 to A11, B0 — Column address (D0 to D35) A0 to A11, B0 — Refresh address (D0 to D35) A0 to A11, B0
DQ0 to DQ71	Data input/output
$\overline{\text{RE}}0$ to $\overline{\text{RE}}3$	Row address strobe ($\overline{\text{RAS}}$)
$\overline{\text{CE}}0$, $\overline{\text{CE}}1$, $\overline{\text{CE}}4$, $\overline{\text{CE}}5$	Column address strobe ($\overline{\text{CAS}}$)
$\overline{\text{WE}}0$, $\overline{\text{WE}}2$	Read/Write enable
$\overline{\text{OE}}0$, $\overline{\text{OE}}2$	Output enable
PD1 to PD8	Presence detect
ID0 , ID1	ID bit
$\overline{\text{PDE}}$	Presence detect enable
V_{CC}	Power supply
V_{SS}	Ground
NC	No connection

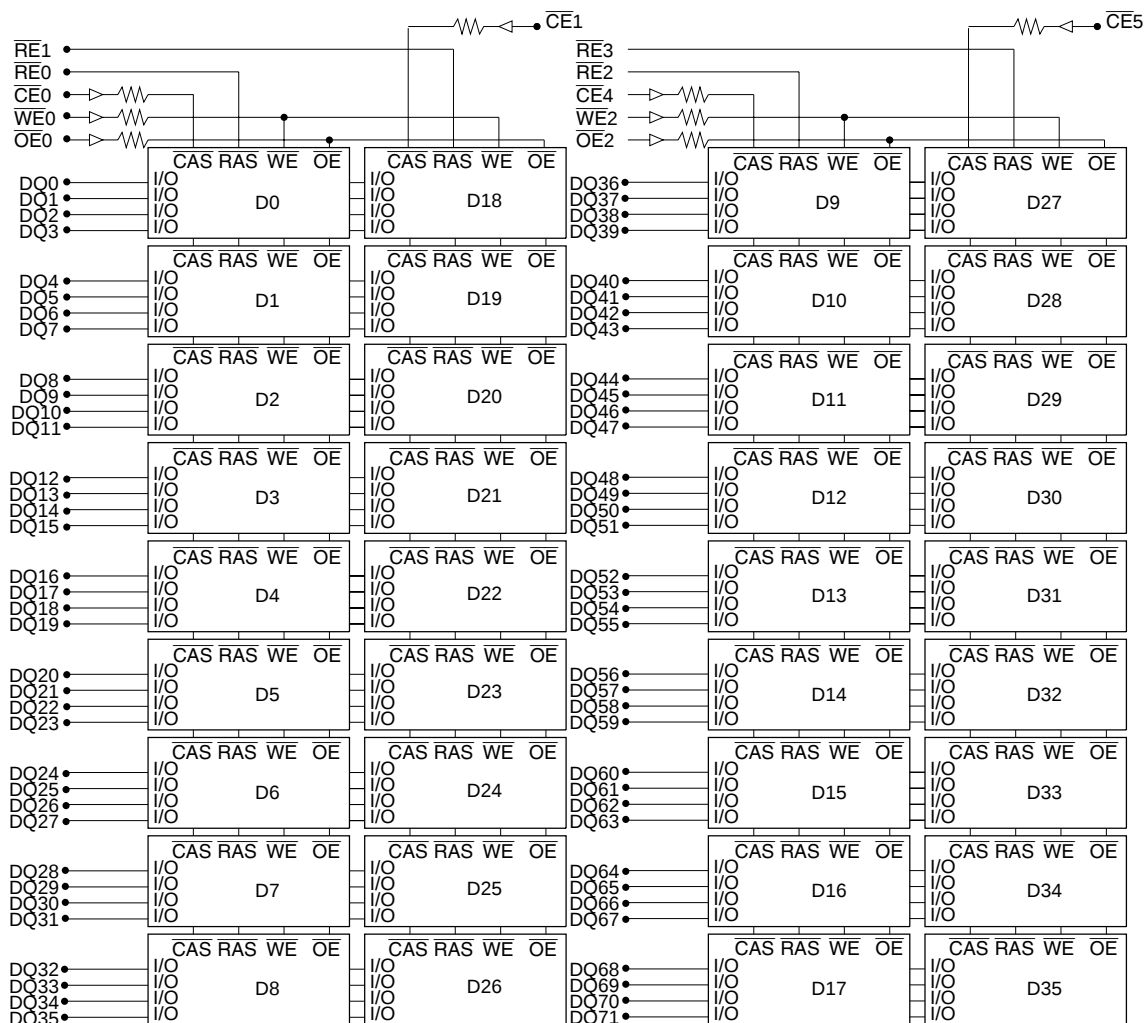
Presence Detect Pin Assignment (Controlled by $\overline{\text{PDE}}$ pin) (HB56UW3273E Series)

Pin name	Pin No.	$\overline{\text{PDE}} = \text{Low}$		$\overline{\text{PDE}} = \text{High}$
		60 ns	70ns	All
PD1	79	1	1	High-Z
PD2	163	0	0	High-Z
PD3	80	0	0	High-Z
PD4	164	0	0	High-Z
PD5	81	1	1	High-Z
PD6	165	1	0	High-Z
PD7	82	1	1	High-Z
PD8	166	0	0	High-Z

Note: 1: High level (driver output). 0: Low level (driver output)

Presence Detect Pin Assignment (Controlled by $\overline{\text{PDE}}$ pin) (HB56UW3273EJ Series)

Pin name	Pin No.	$\overline{\text{PDE}} = \text{Low}$		$\overline{\text{PDE}} = \text{High}$
		60 ns	70ns	All
PD1	79	NC	NC	High-Z
PD2	163	V_{SS}	V_{SS}	High-Z
PD3	80	V_{SS}	V_{SS}	High-Z
PD4	164	V_{SS}	V_{SS}	High-Z
PD5	81	NC	NC	High-Z
PD6	165	NC	V_{SS}	High-Z
PD7	82	NC	NC	High-Z
PD8	166	V_{SS}	V_{SS}	High-Z

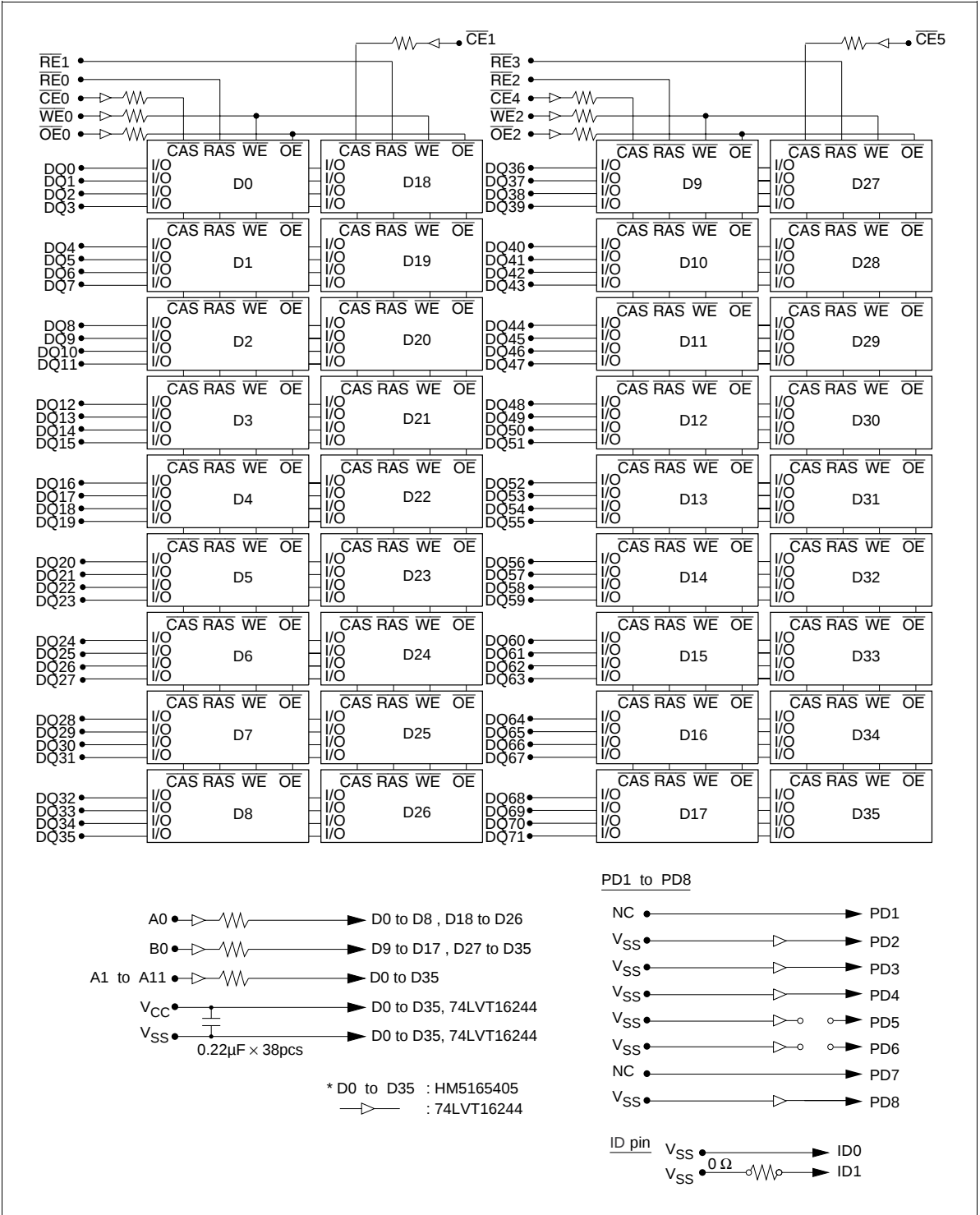


ID pin

V_{SS} $\rightarrow$ ID0

V_{SS} $\xrightarrow{0\ \Omega}$ ID1

Block Diagram (HB56UW3273EJ Series)



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	V_T	−0.5 to +4.6	V
Supply voltage relative to V_{SS}	V_{CC}	−0.5 to +4.6	V
Short circuit output current	I_{out}	50	mA
Power dissipation	P_T	19	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	−55 to +125	°C

Recommended DC Operating Conditions ($T_a = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Supply voltage	V_{CC}	3.0	3.3	3.6	V	1, 2
Input high voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V	1
Input low voltage	V_{IL}	−0.3	—	0.8	V	1

Note: 1. All voltage referred to V_{SS} .
2. The supply voltage with all V_{CC} pins must be on the same level. The supply voltage with all V_{SS} pins must be on the same level.

DC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $V_{SS} = 0\text{ V}$)

HB56UW3273						
Parameter	Symbol	60 ns		70 ns		Unit Test conditions
		Min	Max	Min	Max	
Operating current ^{*1, *2}	I_{CC1}	—	3340	—	2980	mA $t_{RC} = \text{min}$
Standby current	I_{CC2}	—	82	—	82	TTL interface $\overline{RAS}, \overline{CAS} = V_{IH}$ Dout = High-Z
		—	46	—	46	CMOS interface $\overline{RAS}, \overline{CAS} \geq V_{CC} - 0.2\text{ V}$ Dout = High-Z
$\overline{RAS}$ -only refresh current ^{*2}	I_{CC3}	—	3340	—	2980	mA $t_{RC} = \text{min}$
Standby current ^{*1}	I_{CC5}	—	190	—	190	mA $\overline{RAS} = V_{IH}, \overline{CAS} = V_{IL}$ Dout = enable
$\overline{CAS}$ -before- $\overline{RAS}$ refresh current	I_{CC6}	—	2800	—	2440	mA $t_{RC} = \text{min}$
EDO page mode current ^{*1, *3}	I_{CC7}	—	2620	—	2260	mA $t_{HPC} = \text{min}$
Input leakage current	I_{LI}	-10	10	-10	10	μA $0\text{ V} \leq V_{in} \leq 4.6\text{ V}$
Output leakage current	I_{LO}	-10	10	-10	10	μA $0\text{ V} \leq V_{in} \leq 4.6\text{ V}$ Dout = disable
Output high voltage	V_{OH}	2.4	V_{CC}	2.4	V_{CC}	V High Iout = -2 mA
Output low voltage	V_{OL}	0	0.4	0	0.4	V Low Iout = 2 mA

- Notes : 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.
 2. Address can be changed once or less while $\overline{RAS} = V_{IL}$.
 3. Address can be changed once or less within one page mode cycle t_{HPC} .

Capacitance ($T_a = 25^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$)

Parameter	Symbol	Typ	Max	Unit	Notes
Input capacitance (Address)	C_{I1}	—	20	pF	1
Input capacitance ($\overline{CAS}$, $\overline{WE}$, $\overline{OE}$)	C_{I2}	—	20	pF	1
Input capacitance ($\overline{RAS}$)	C_{I3}	—	78	pF	1
I/O capacitance (DQ)	$C_{I/O}$	—	30	pF	1, 2

- Notes : 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.
 2. $\overline{CAS} = V_{IH}$ to disable Dout.

AC Characteristics (Ta = 0 to +70°C, VCC = 3.3 V ± 0.3 V, VSS = 0 V) *1, *2, *3, *18

Test Conditions

- Input rise and fall time: 2 ns
- Input levels: VIL = 0 V, VIH = 3 V
- Input timing reference levels: 0.8 V, 2.0 V
- Output timing reference levels: 0.8 V, 2.0 V
- Output load: 1 TTL gate + CL (100 pF) (Including scope and jig)

Read, Write, Read-Modify-Write and Refresh Cycles (Common parameters)

HB56UW3273							
Parameter	Symbol	60 ns		70 ns		Unit	Notes
		Min	Max	Min	Max		
Random read or write cycle time	t _{RC}	104	—	124	—	ns	
RAS precharge time	t _{RP}	40	—	50	—	ns	
CAS precharge time	t _{CP}	10	—	13	—	ns	
RAS pulse width	t _{RAS}	60	10000	70	10000	ns	
CAS pulse width	t _{CAS}	10	10000	13	10000	ns	
Row address setup time	t _{ASR}	5	—	5	—	ns	
Row address hold time	t _{RAH}	10	—	10	—	ns	
Column address setup time	t _{ASC}	0	—	0	—	ns	
Column address hold time	t _{CAH}	10	—	13	—	ns	
RAS to CAS delay time	t _{RCD}	20	40	20	47	ns	3
RAS to column address delay time	t _{RAD}	15	25	15	30	ns	4
RAS hold time	t _{RSH}	20	—	23	—	ns	
CAS hold time	t _{CSH}	48	—	58	—	ns	21
CAS to RAS precharge time	t _{CRP}	10	—	10	—	ns	
OE to Din delay time	t _{OED}	20	—	23	—	ns	5
OE delay time from Din	t _{DZO}	0	—	0	—	ns	6
CAS delay time from Din	t _{DZC}	0	—	0	—	ns	6
Transition time (rise and fall)	t _T	2	50	2	50	ns	7

Read Cycle

		HB56UW3273					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Access time from $\overline{\text{RAS}}$	t_{RAC}	—	60	—	70	ns	8, 9
Access time from $\overline{\text{CAS}}$	t_{CAC}	—	20	—	23	ns	9, 10, 16
Access time from address	t_{AA}	—	35	—	40	ns	9, 11, 16
Access time from $\overline{\text{OE}}$	t_{OEA}	—	20	—	23	ns	9
Read command setup time	t_{RCS}	0	—	0	—	ns	
Read command hold time to $\overline{\text{CAS}}$	t_{RCH}	0	—	0	—	ns	12
Read command hold time from $\overline{\text{RAS}}$	t_{RCHR}	60	—	70	—	ns	
Read command hold time to $\overline{\text{RAS}}$	t_{RRH}	0	—	0	—	ns	12
Column address to $\overline{\text{RAS}}$ lead time	t_{RAL}	35	—	40	—	ns	
Column address to $\overline{\text{CAS}}$ lead time	t_{CAL}	18	—	23	—	ns	
$\overline{\text{CAS}}$ to output in low-Z	t_{CLZ}	2	—	2	—	ns	
Output data hold time	t_{OH}	3	—	3	—	ns	
Output data hold time from $\overline{\text{OE}}$	t_{OHO}	3	—	3	—	ns	
Output buffer turn-off time	t_{OFF}	—	20	—	20	ns	13, 20
Output buffer turn-off to $\overline{\text{OE}}$	t_{OEZ}	—	20	—	20	ns	13
$\overline{\text{CAS}}$ to Din delay time	t_{CDD}	20	—	23	—	ns	5
Output data hold time from $\overline{\text{RAS}}$	t_{OHR}	3	—	3	—	ns	
Output buffer turn-off to $\overline{\text{RAS}}$	t_{OFR}	—	15	—	15	ns	20
Output buffer turn-off to $\overline{\text{WE}}$	t_{WEZ}	—	20	—	20	ns	
$\overline{\text{WE}}$ to Din delay time	t_{WED}	20	—	23	—	ns	
$\overline{\text{RAS}}$ to Din delay time	t_{RDD}	15	—	18	—	ns	

HB56UW3273 Series

Write Cycle

Parameter		HB56UW3273				Unit	Notes
		60 ns		70 ns			
		Min	Max	Min	Max		
Write command setup time	t _{WCS}	0	—	0	—	ns	14
Write command hold time	t _{WCH}	10	—	13	—	ns	
Write command pulse width	t _{WP}	10	—	10	—	ns	
Write command to $\overline{\text{RAS}}$ lead time	t _{RWL}	15	—	18	—	ns	
Write command to $\overline{\text{CAS}}$ lead time	t _{CWL}	10	—	13	—	ns	
Data-in setup time	t _{DS}	0	—	0	—	ns	
Data-in hold time	t _{DH}	15	—	18	—	ns	

Read-Modify-Write Cycle

Parameter		HB56UW3273				Unit	Notes
		60 ns		70 ns			
		Min	Max	Min	Max		
Read-modify-write cycle time	t _{RWC}	154	—	180	—	ns	
RAS to $\overline{\text{WE}}$ delay time	t _{RWD}	83	—	96	—	ns	14
CAS to $\overline{\text{WE}}$ delay time	t _{CWD}	33	—	39	—	ns	14
Column address to $\overline{\text{WE}}$ delay time	t _{AWD}	48	—	56	—	ns	14
$\overline{\text{OE}}$ hold time from $\overline{\text{WE}}$	t _{OEH}	15	—	18	—	ns	

Refresh Cycle

Parameter		HB56UW3273				Unit	Notes
		60 ns		70 ns			
		Min	Max	Min	Max		
$\overline{\text{CAS}}$ setup time (CBR refresh cycle)	t _{CSR}	10	—	10	—	ns	
$\overline{\text{CAS}}$ hold time (CBR refresh cycle)	t _{CHR}	10	—	10	—	ns	
$\overline{\text{WE}}$ setup time (CBR refresh cycle)	t _{WRP}	5	—	5	—	ns	
$\overline{\text{WE}}$ hold time (CBR refresh cycle)	t _{WRH}	10	—	10	—	ns	
$\overline{\text{RAS}}$ precharge to $\overline{\text{CAS}}$ hold time	t _{RPC}	0	—	0	—	ns	

EDO Page Mode Cycle

		HB56UW3273					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
EDO page mode cycle time	t _{HPC}	25	—	30	—	ns	19
EDO page mode $\overline{\text{RAS}}$ pulse width	t _{RASP}	—	100000	—	100000	ns	15
Access time from $\overline{\text{CAS}}$ precharge	t _{CPA}	—	40	—	45	ns	9, 16
$\overline{\text{RAS}}$ hold time from $\overline{\text{CAS}}$ precharge	t _{CPRH}	40	—	45	—	ns	
Output data hold time from $\overline{\text{CAS}}$ low	t _{DOH}	3	—	3	—	ns	9, 16
$\overline{\text{CAS}}$ hold time referred $\overline{\text{OE}}$	t _{COL}	10	—	13	—	ns	
$\overline{\text{CAS}}$ to $\overline{\text{OE}}$ setup time	t _{COP}	10	—	10	—	ns	
Read command hold time from $\overline{\text{CAS}}$ precharge	t _{RCHC}	35	—	40	—	ns	
Write pulse width during $\overline{\text{CAS}}$ precharge	t _{WPE}	10	—	10	—	ns	
$\overline{\text{OE}}$ precharge time	t _{OEP}	10	—	10	—	ns	

EDO Page Mode Read-Modify-Write Cycle

		HB56UW3273					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
EDO page mode read- modify-write cycle time	t _{HPRWC}	68	—	79	—	ns	
$\overline{WE}$ delay time from $\overline{CAS}$ precharge	t _{CPW}	54	—	62	—	ns	14

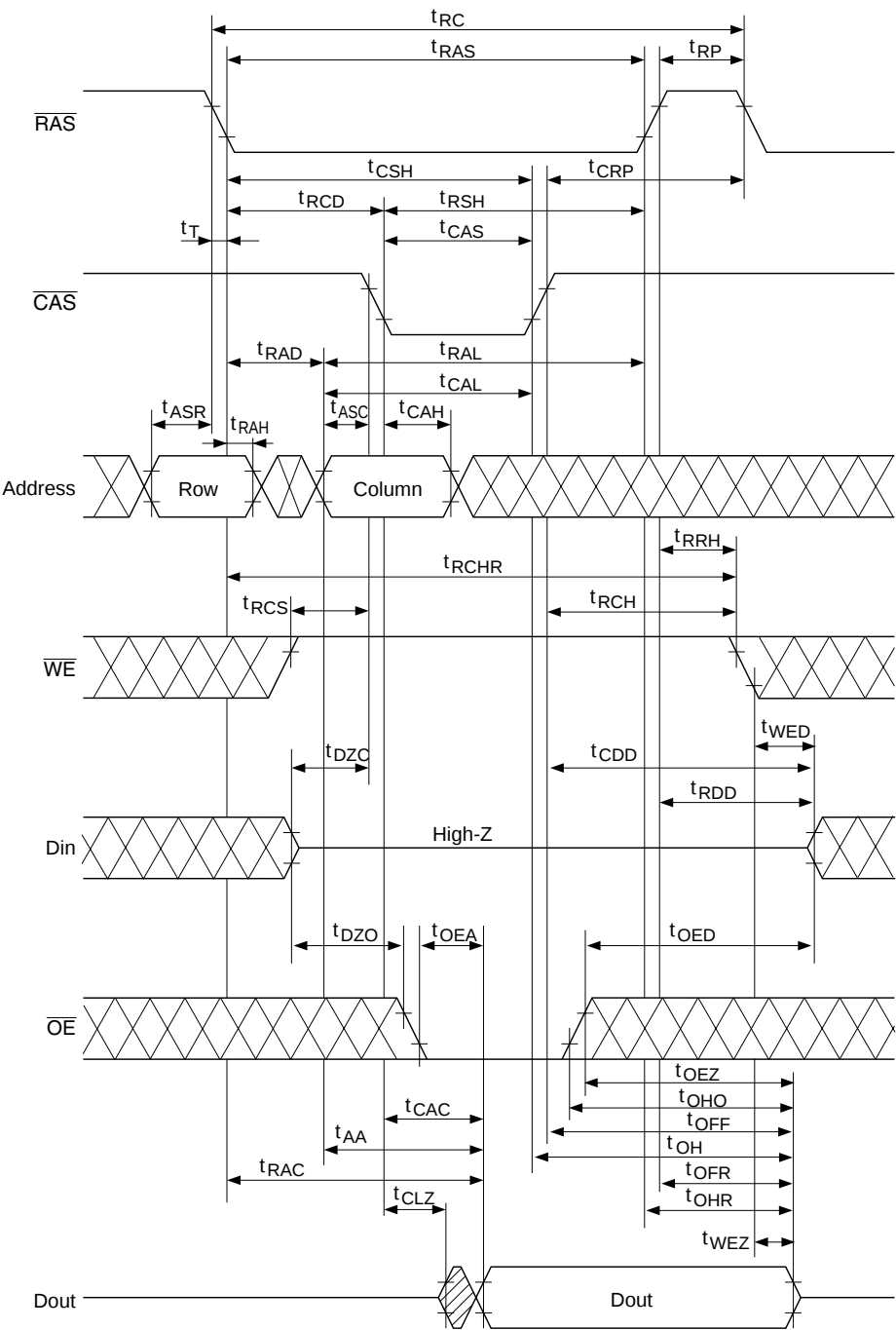
Refresh

Parameter	Symbol	Max	Unit	Notes
Refresh period	t_{REF}	64	ms	4096 cycles

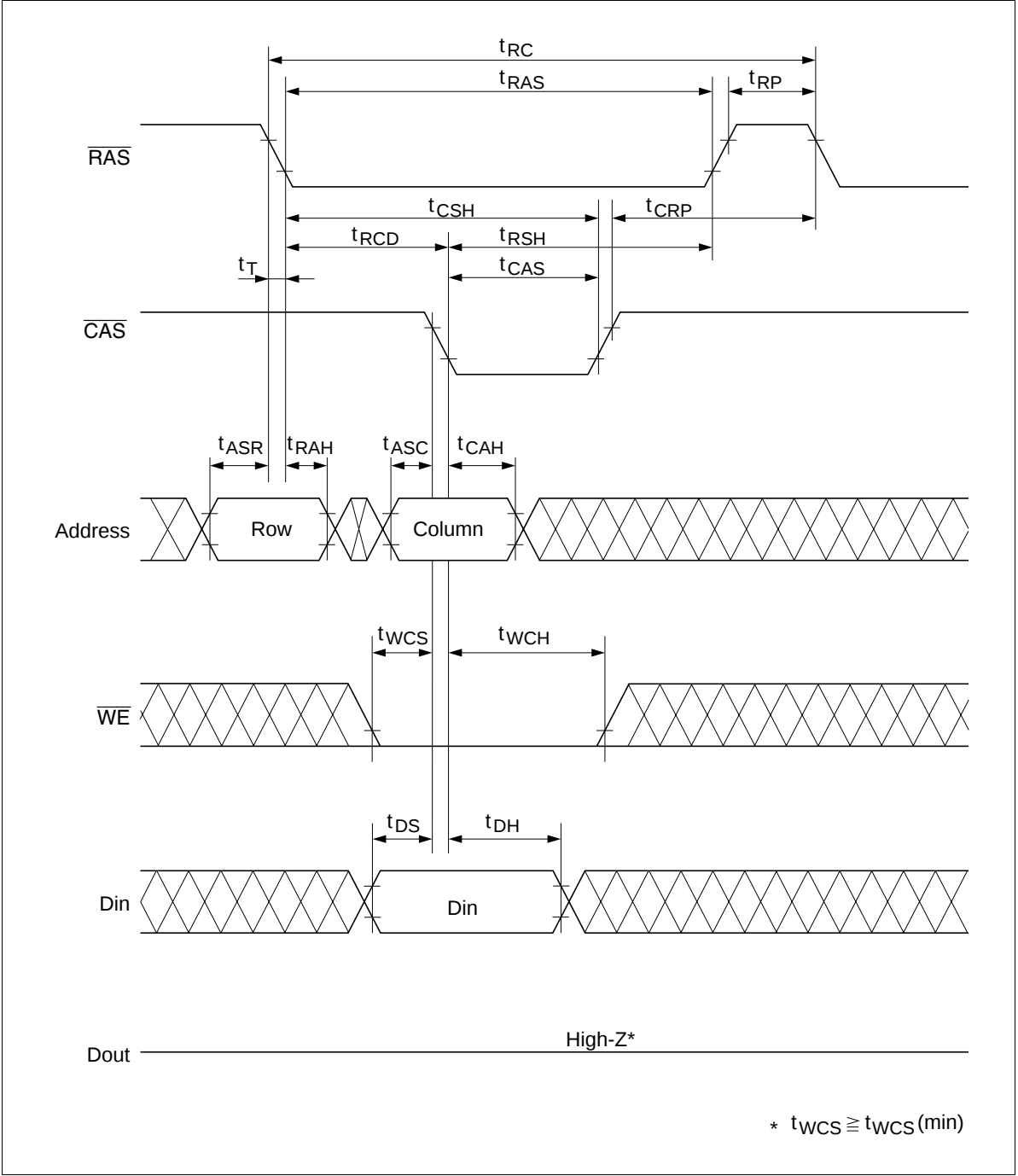
- Notes:
1. AC measurements assume $t_r = 2$ ns.
 2. An initial pause of 200 μ s is required after power up followed by a minimum of eight initialization cycles (any combination of cycles containing RAS-only refresh or CAS-before-RAS refresh).
 3. Operation with the t_{RCD} (max) limit insures that t_{RAC} (max) can be met, t_{RCD} (max) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (max) limit, then access time is controlled exclusively by t_{CAC} .
 4. Operation with the t_{RAD} (max) limit insures that t_{RAC} (max) can be met, t_{RAD} (max) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (max) limit, then access time is controlled exclusively by t_{AA} .
 5. Either t_{OED} or t_{CDD} must be satisfied.
 6. Either t_{DZO} or t_{DZC} must be satisfied.
 7. V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} (min) and V_{IL} (max).
 8. Assumes that $t_{RCD} \leq t_{RCD}$ (max) and $t_{RAD} \leq t_{RAD}$ (max). If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
 9. Measured with a load circuit equivalent to 1 TTL loads and 100 pF.
 10. Assumes that $t_{RCD} \geq t_{RCD}$ (max) and $t_{RCD} + t_{CAC}$ (max) $\geq t_{RAD} + t_{AA}$ (max).
 11. Assumes that $t_{RAD} \geq t_{RAD}$ (max) and $t_{RCD} + t_{CAC}$ (max) $\leq t_{RAD} + t_{AA}$ (max).
 12. Either t_{RCH} or t_{RRH} must be satisfied for a read cycles.
 13. t_{OFF} (max), t_{OEZ} (max), t_{WEZ} (max) and t_{OFR} (max) define the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.
 14. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPW} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if $t_{WCS} \geq t_{WCS}$ (min), the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{RWD} \geq t_{RWD}$ (min), $t_{CWD} \geq t_{CWD}$ (min), and $t_{AWD} \geq t_{AWD}$ (min), or $t_{CWD} \geq t_{CWD}$ (min), $t_{AWD} \geq t_{AWD}$ (min) and $t_{CPW} \geq t_{CPW}$ (min), the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
 15. t_{RASP} defines $\overline{RAS}$ pulse width in EDO page mode cycles.
 16. Access time is determined by the longest among t_{AA} , t_{CAC} and t_{CPA} .
 17. All the V_{CC} and V_{SS} pins shall be supplied with the same voltages.
 18. In delayed write or read-modify-write cycles, $\overline{OE}$ must disable output buffer prior to applying data to the device.
 19. t_{HPC} (min) can be achieved during a series of EDO page mode write cycles or EDO page mode read cycles. If both write and read operation are mixed in a EDO page mode $\overline{RAS}$ cycle (EDO page mode mix cycle (1), (2)), minimum value of $\overline{CAS}$ cycle ($t_{CAS} + t_{CP} + 2 t_r$) becomes greater than the specified t_{HPC} (min) value. The value of $\overline{CAS}$ cycle time of mixed EDO page mode is shown in EDO page mode mix cycle (1) and (2).
 20. Output is disable after both $\overline{RAS}$ and $\overline{CAS}$ go to high.
 21. t_{CSH} (min) can be achieved when $t_{RCD} \leq t_{CSH}$ (min) - t_{CAS} (min).
 22. XXX: H or L (H: V_{IH} (min) $\leq V_{IN} \leq V_{IH}$ (max), L: V_{IL} (min) $\leq V_{IN} \leq V_{IL}$ (max))
/////: Invalid Dout
- When the address, clock and input pins are not described on timing waveforms, their pins must be applied V_{IH} or V_{IL} .

Timing Waveforms*22

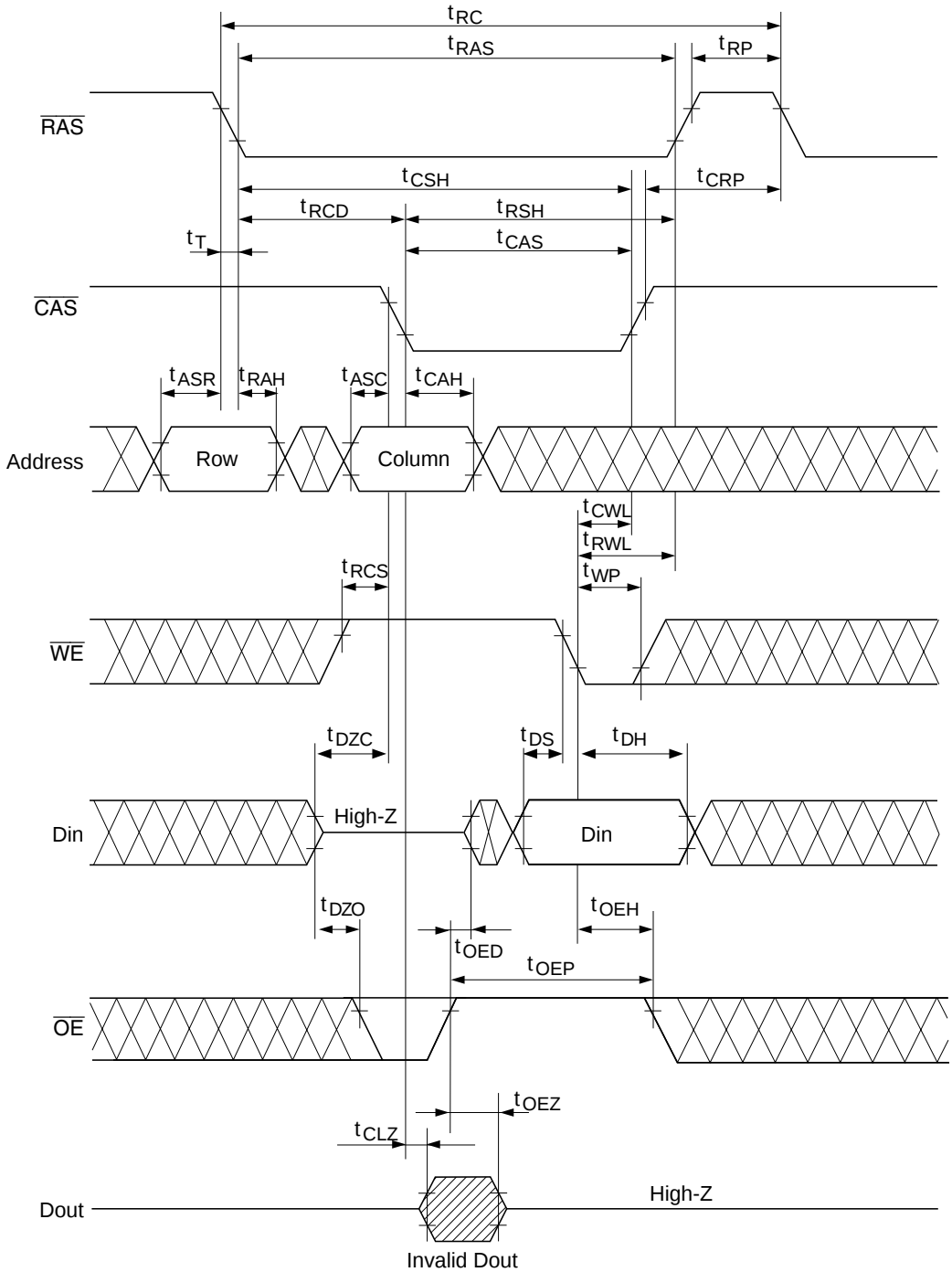
Read Cycle



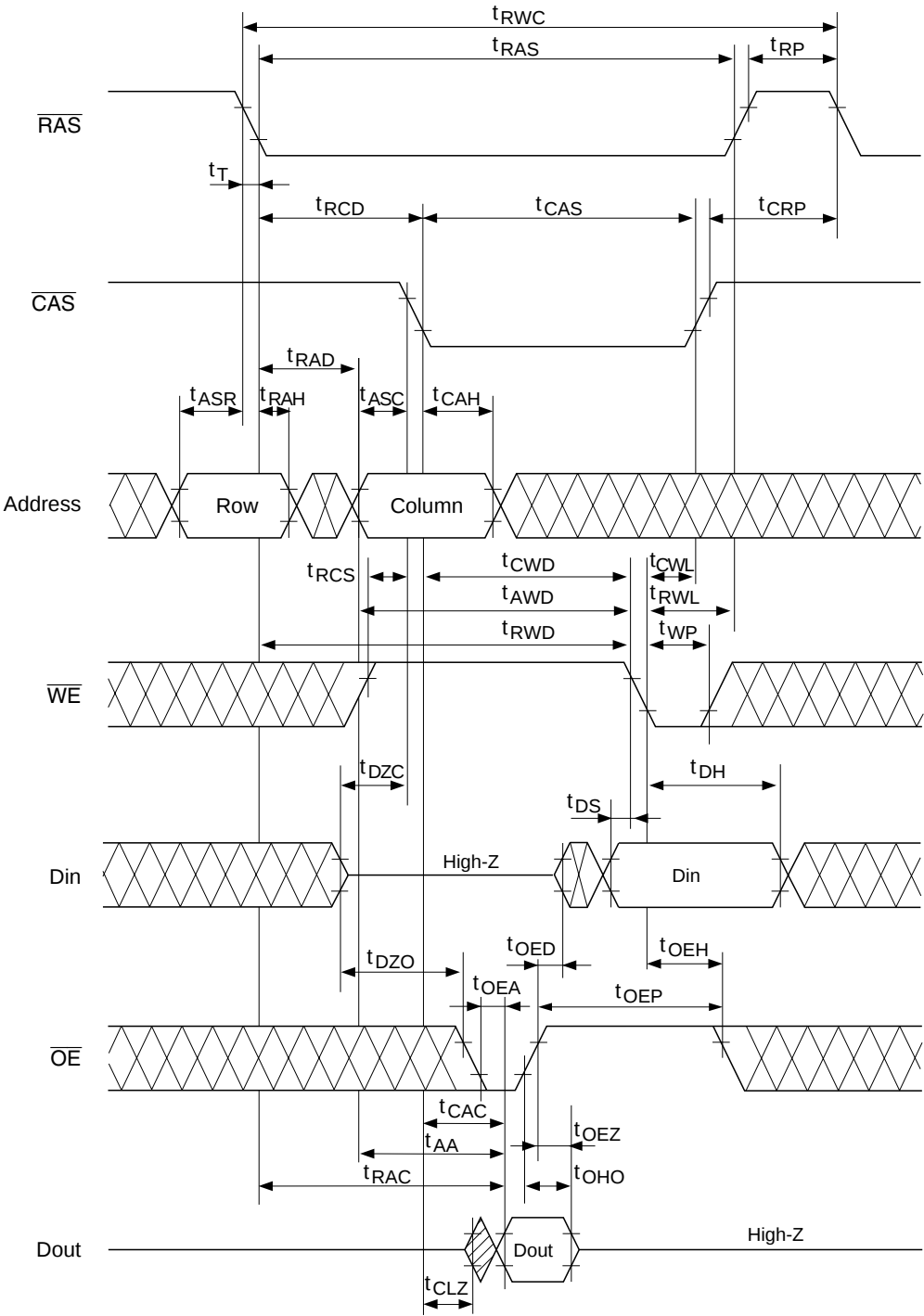
Early Write Cycle



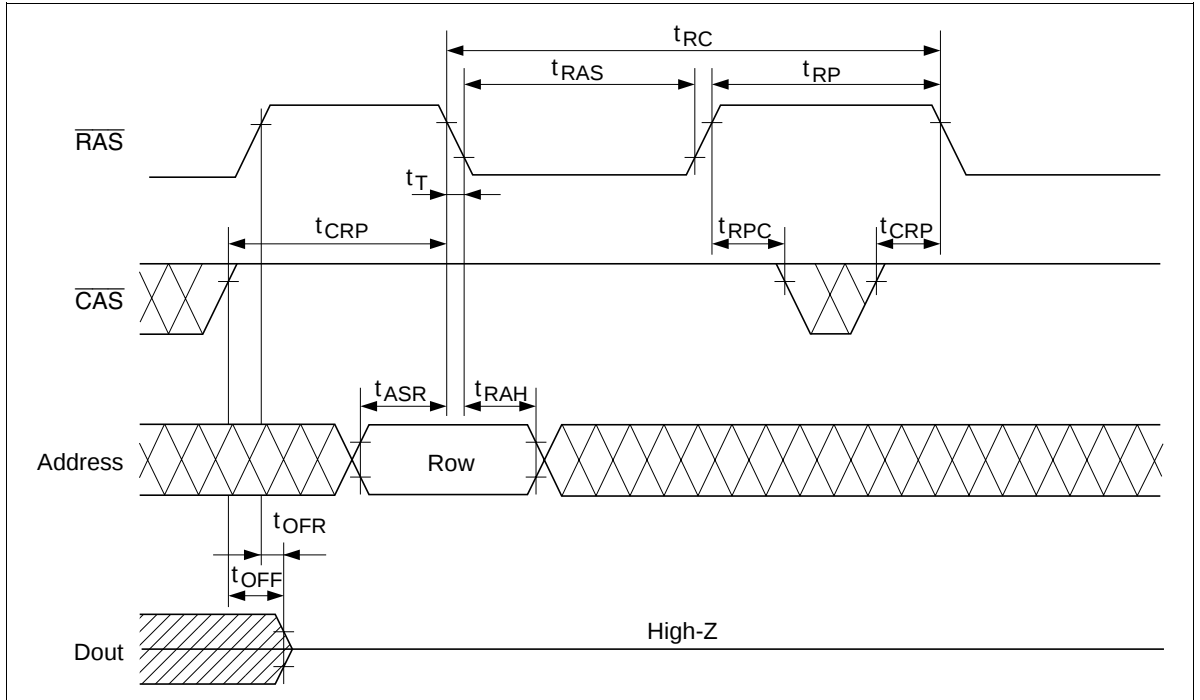
Delayed Write Cycle*18



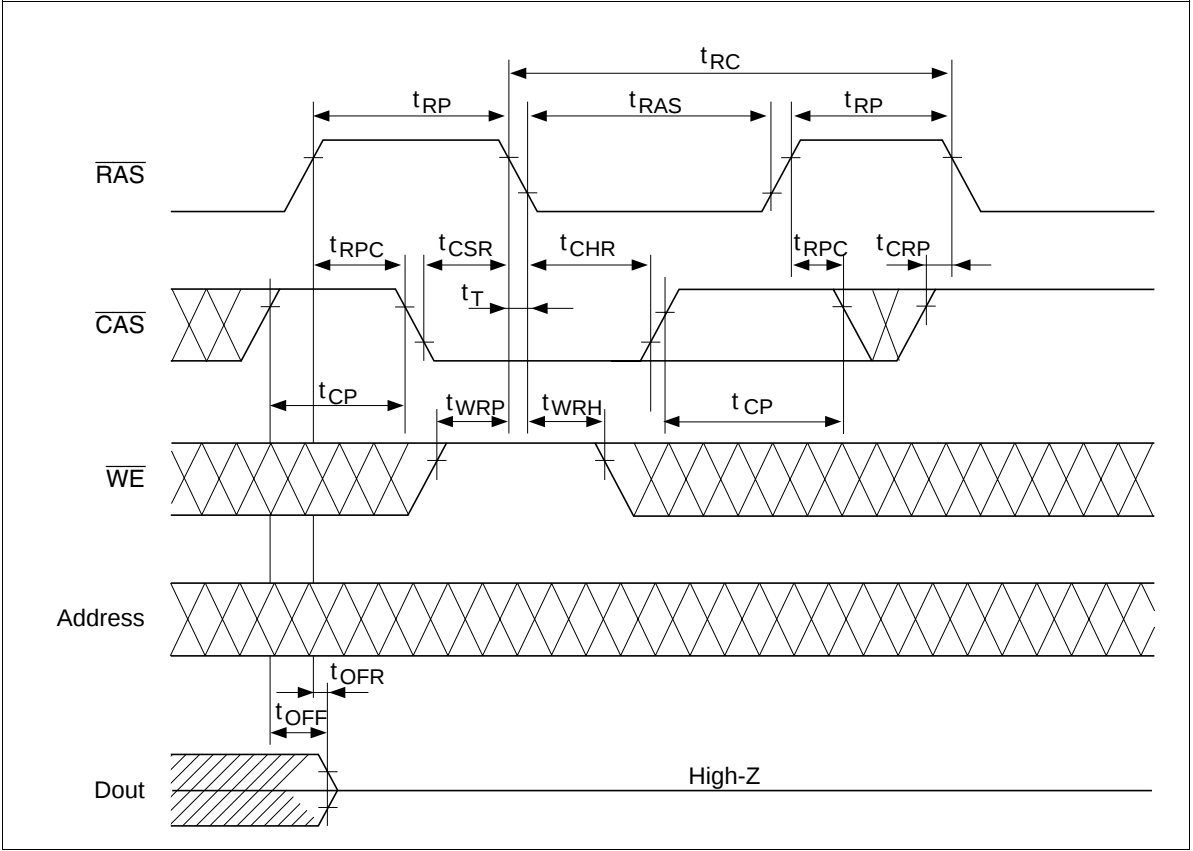
Read-Modify-Write Cycle*18



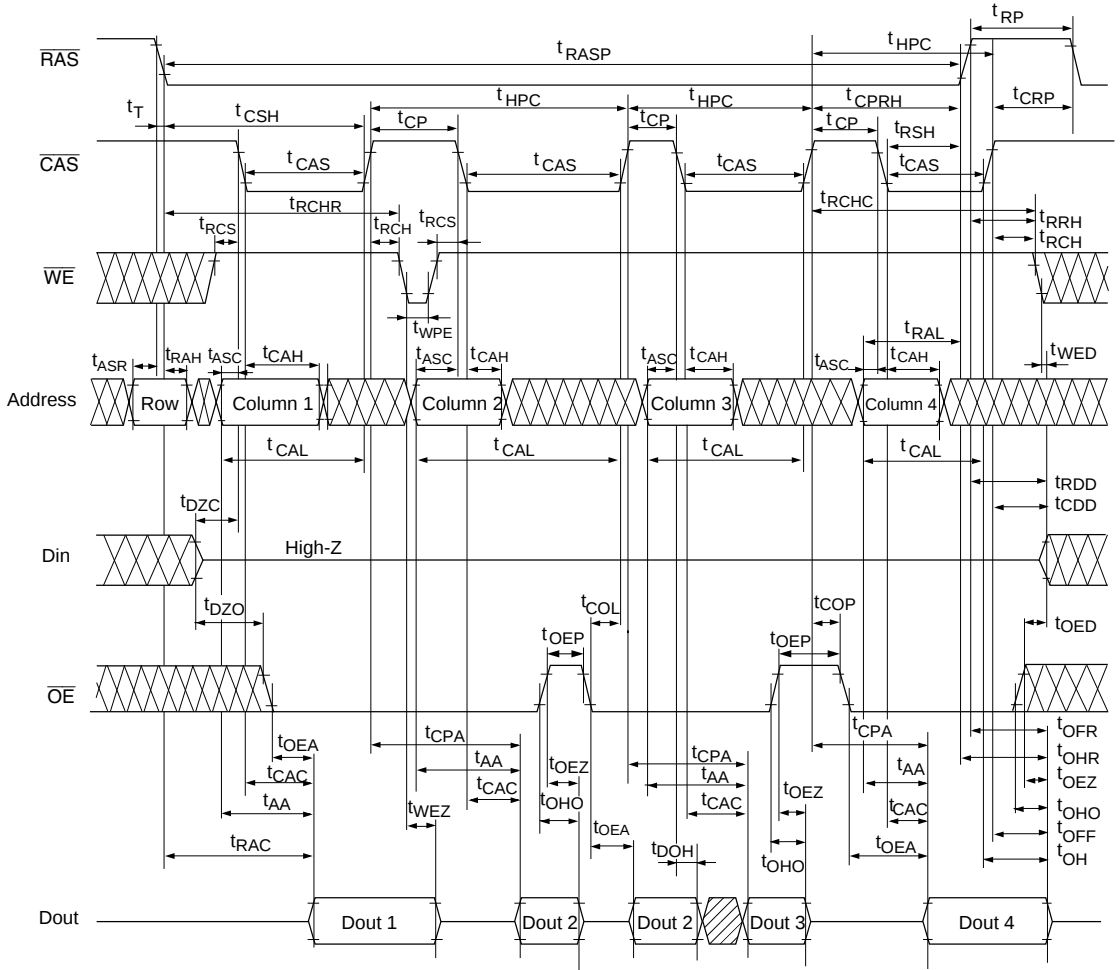
RAS-Only Refresh Cycle



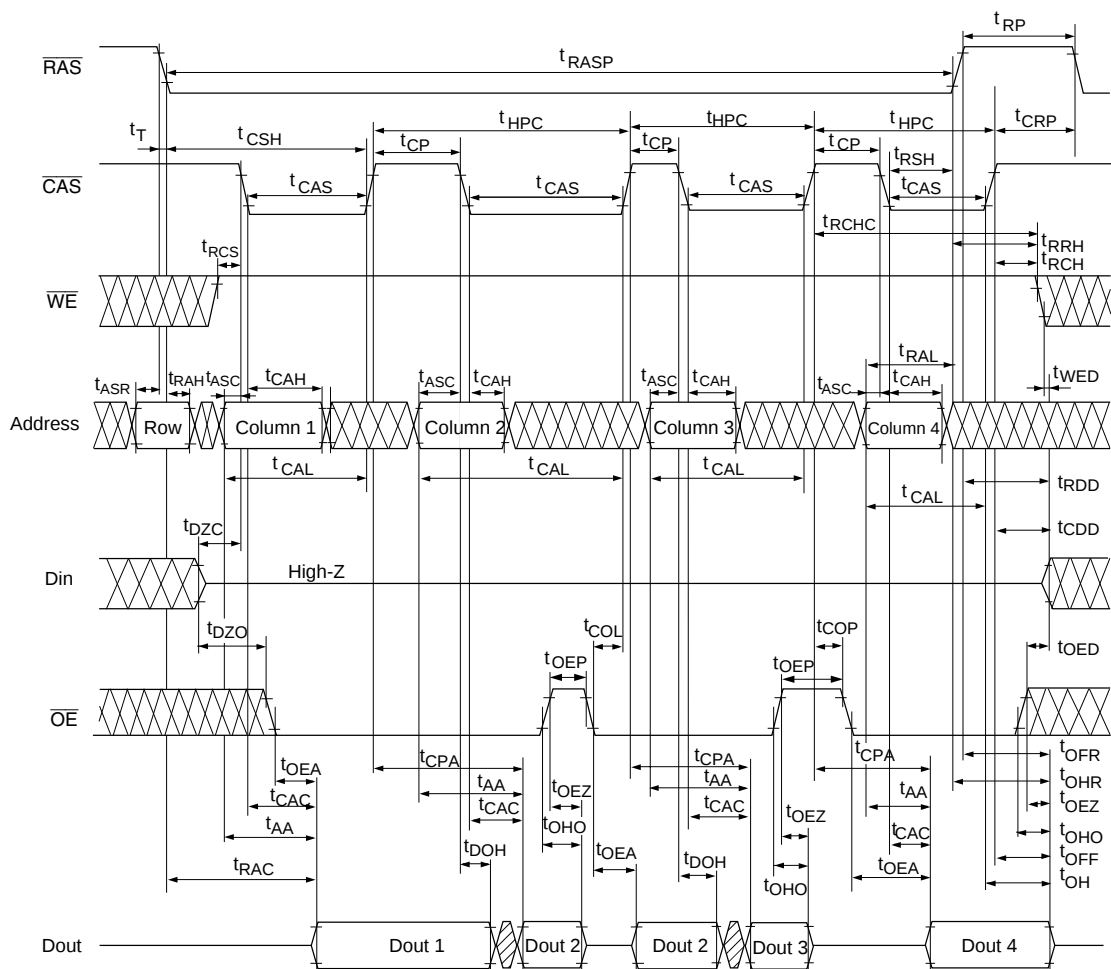
CAS-Before-RAS Refresh Cycle



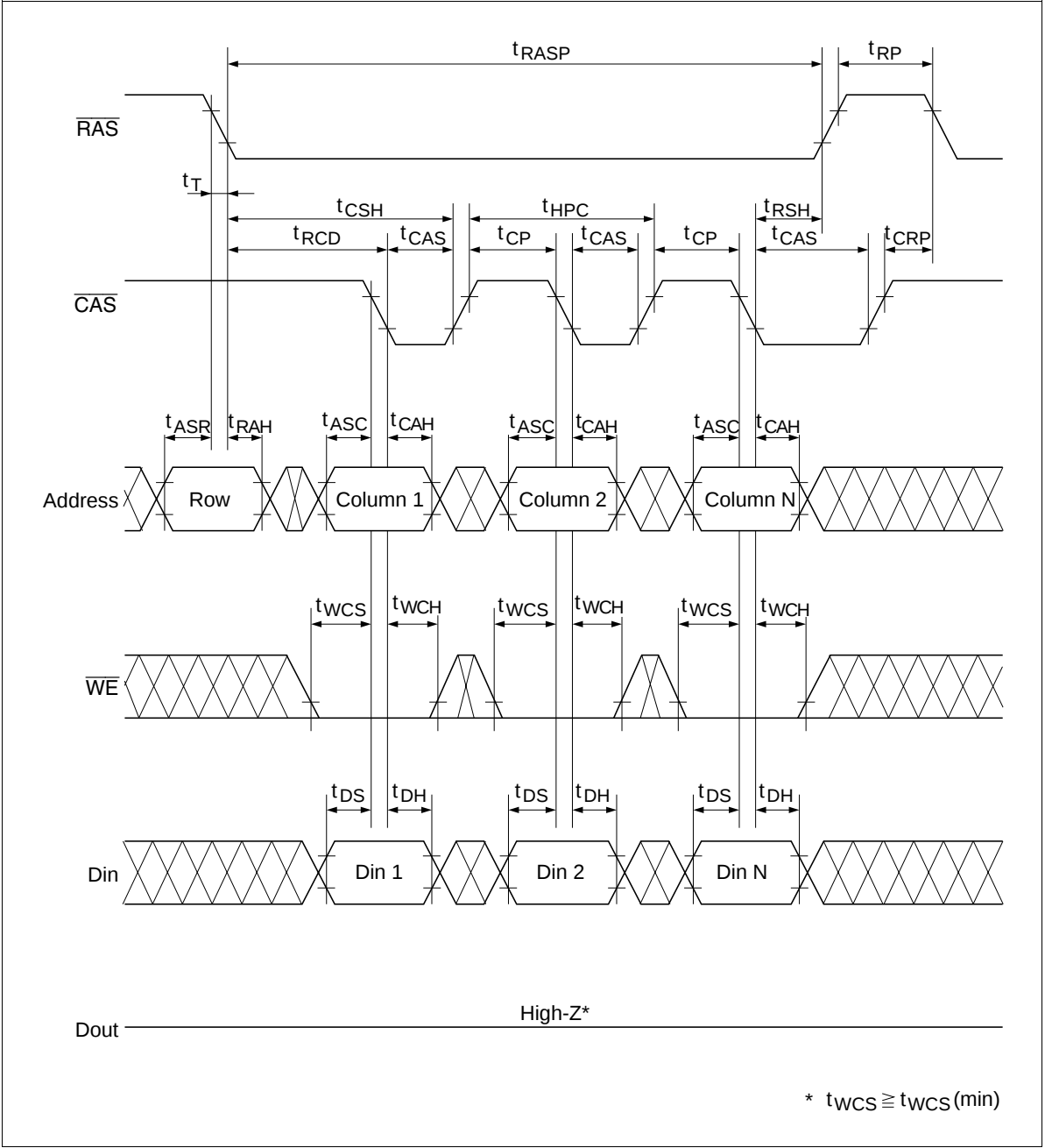
EDO Page Mode Read Cycle (1)



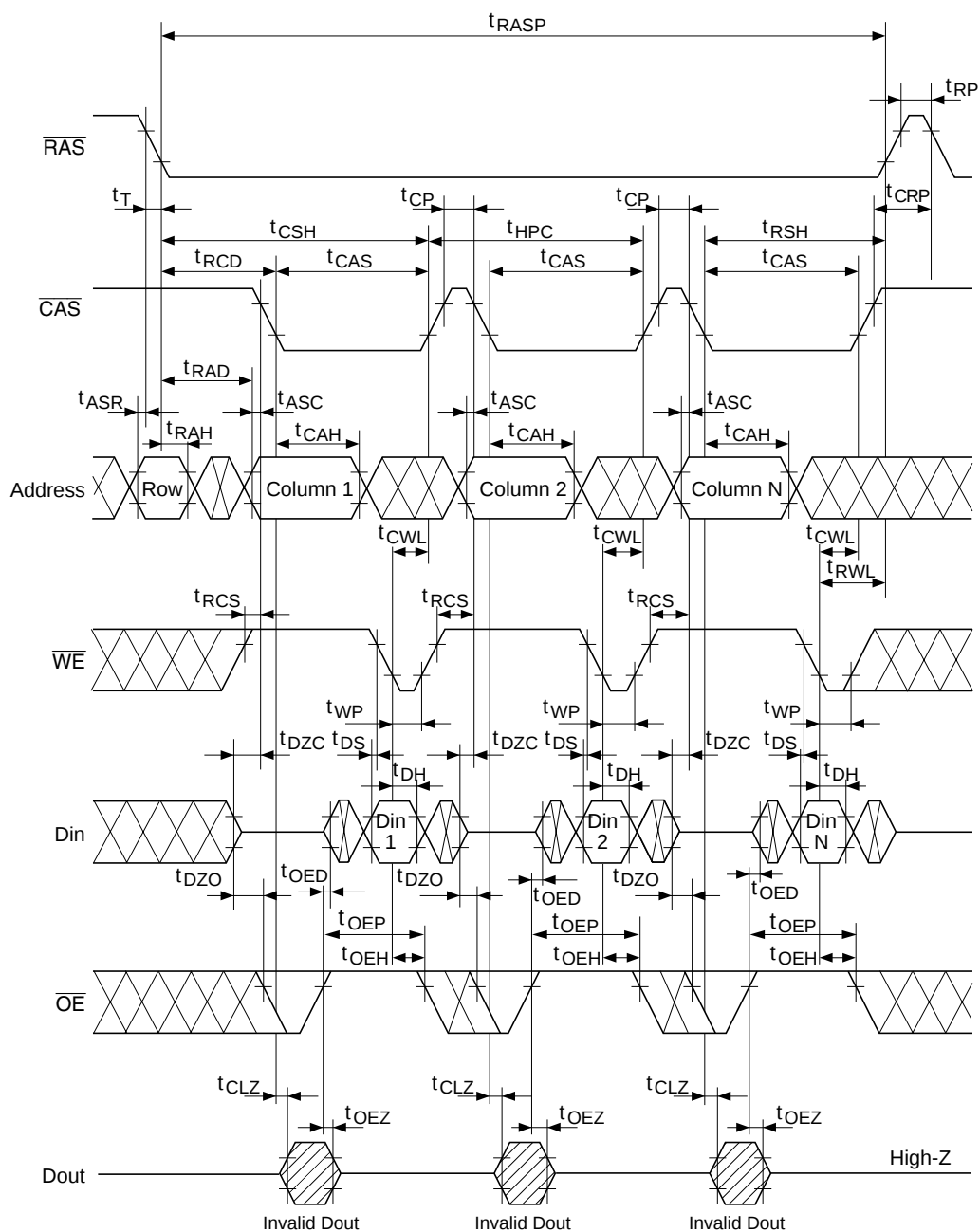
EDO Page Mode Read Cycle (2)



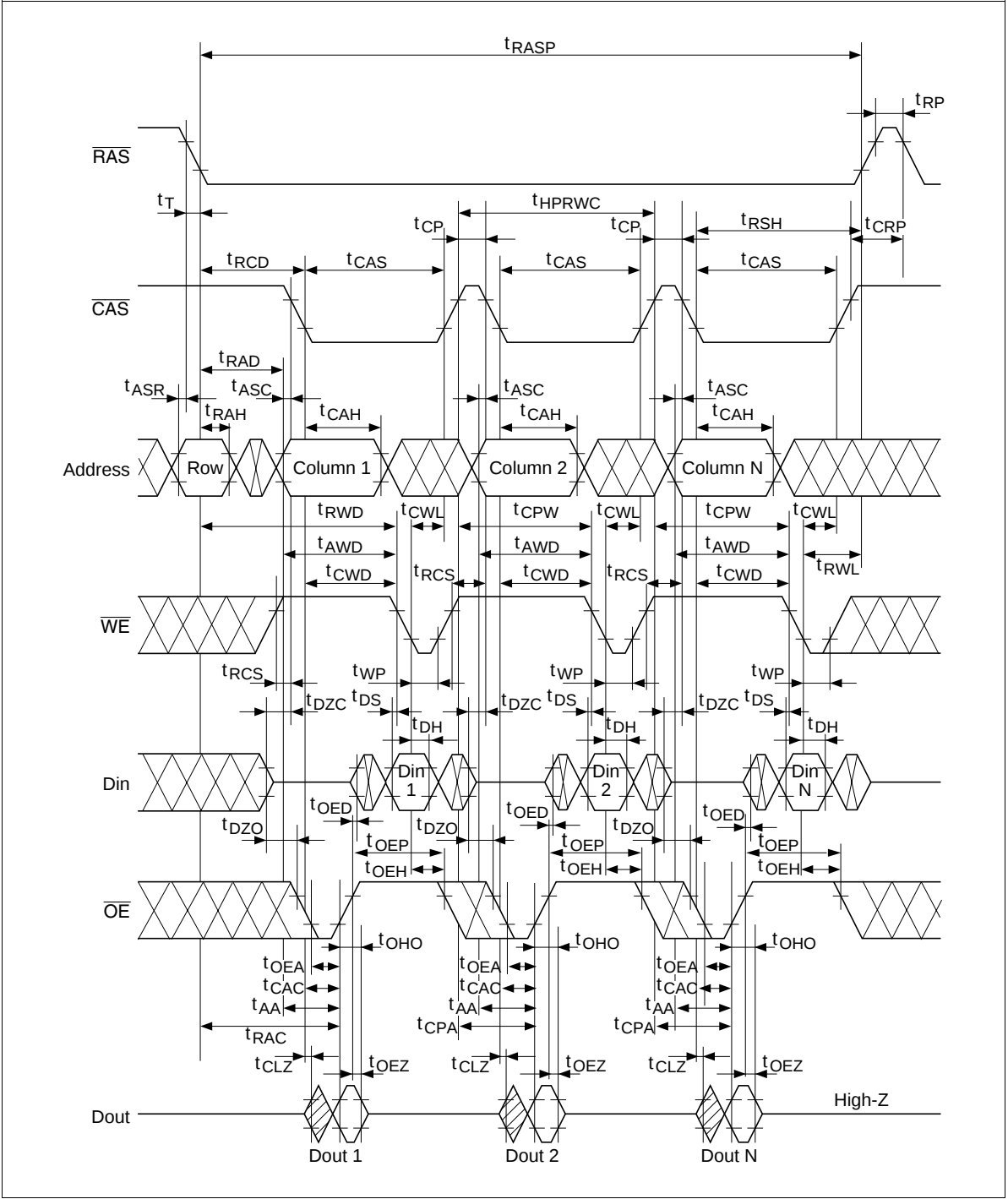
EDO Page Mode Early Write Cycle



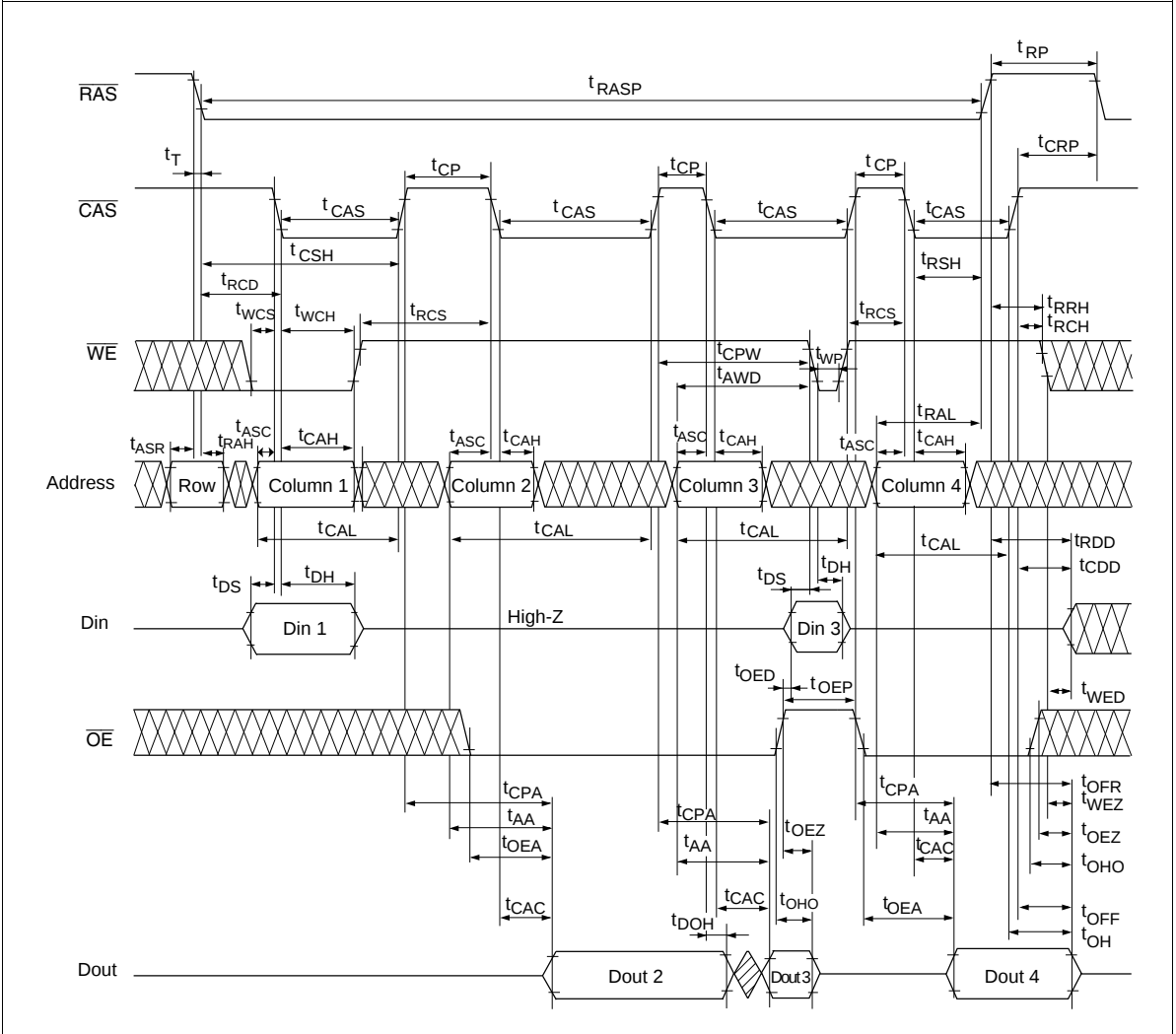
EDO Page Mode Delayed Write Cycle*¹⁸



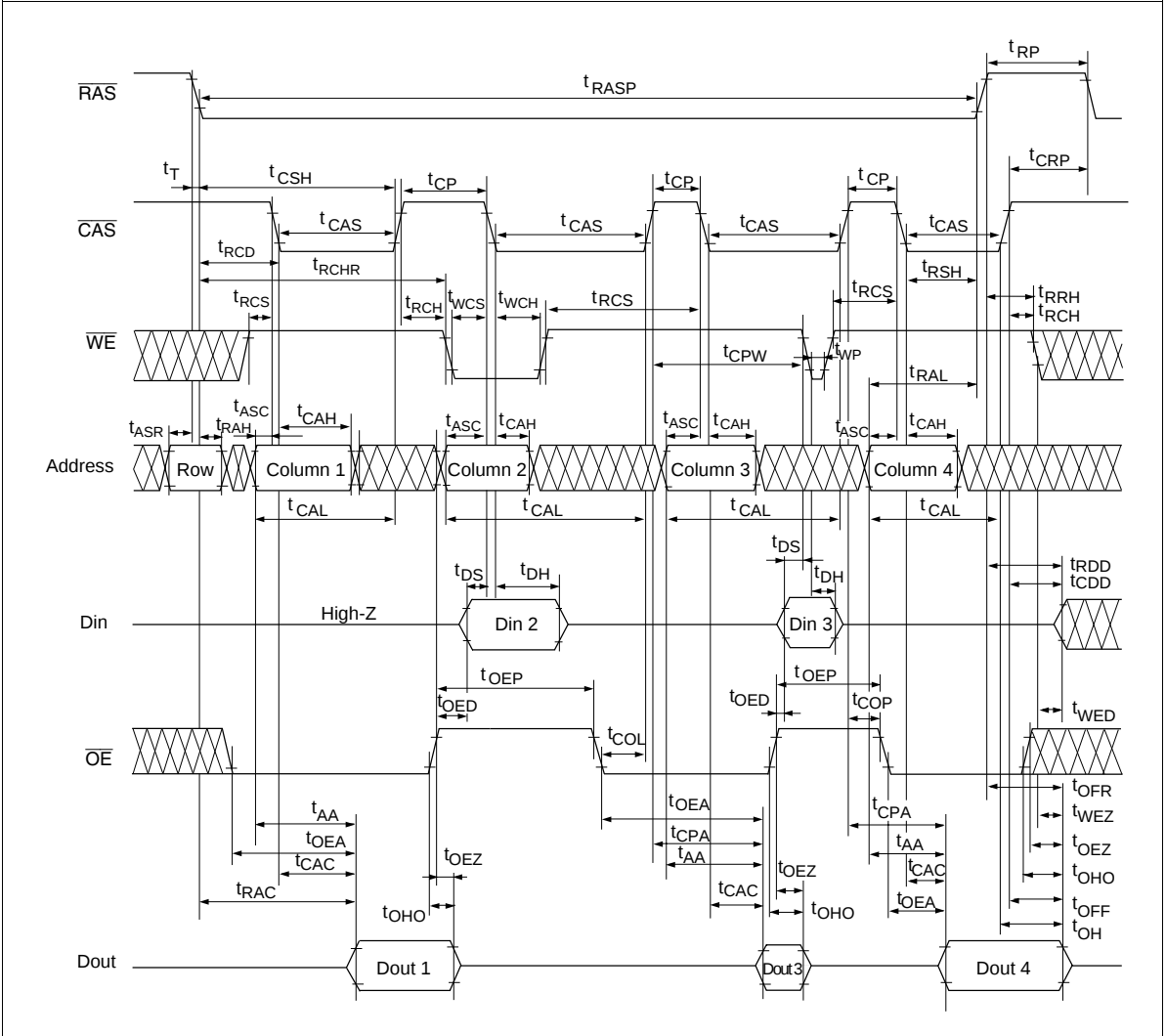
EDO Page Mode Read-Modify-Write Cycle*18



EDO Page Mode Mix Cycle (1)



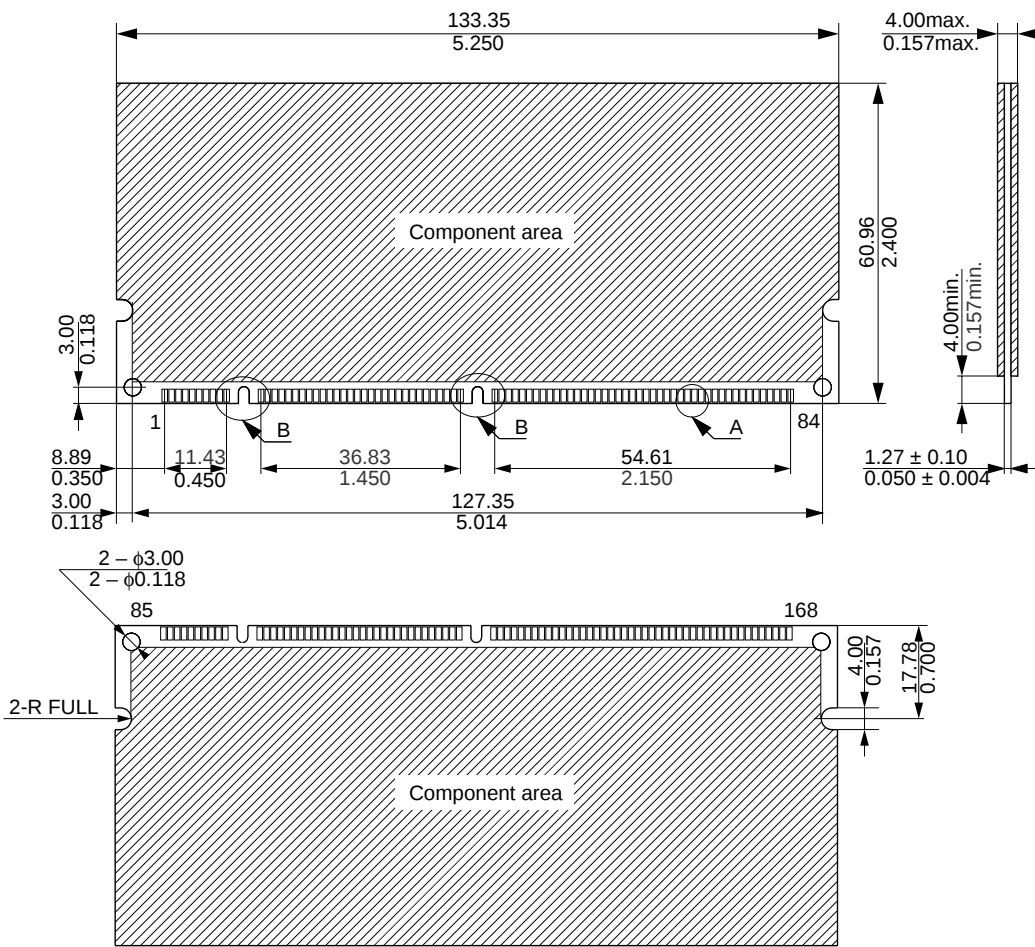
EDO Page Mode Mix Cycle (2)



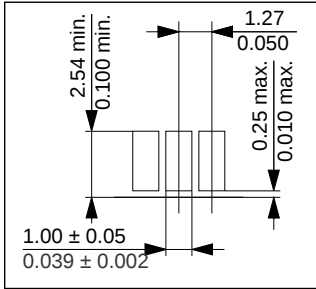
Physical Outline

HB56UW3273E Series

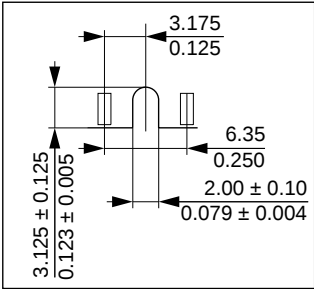
Unit: mm/inch

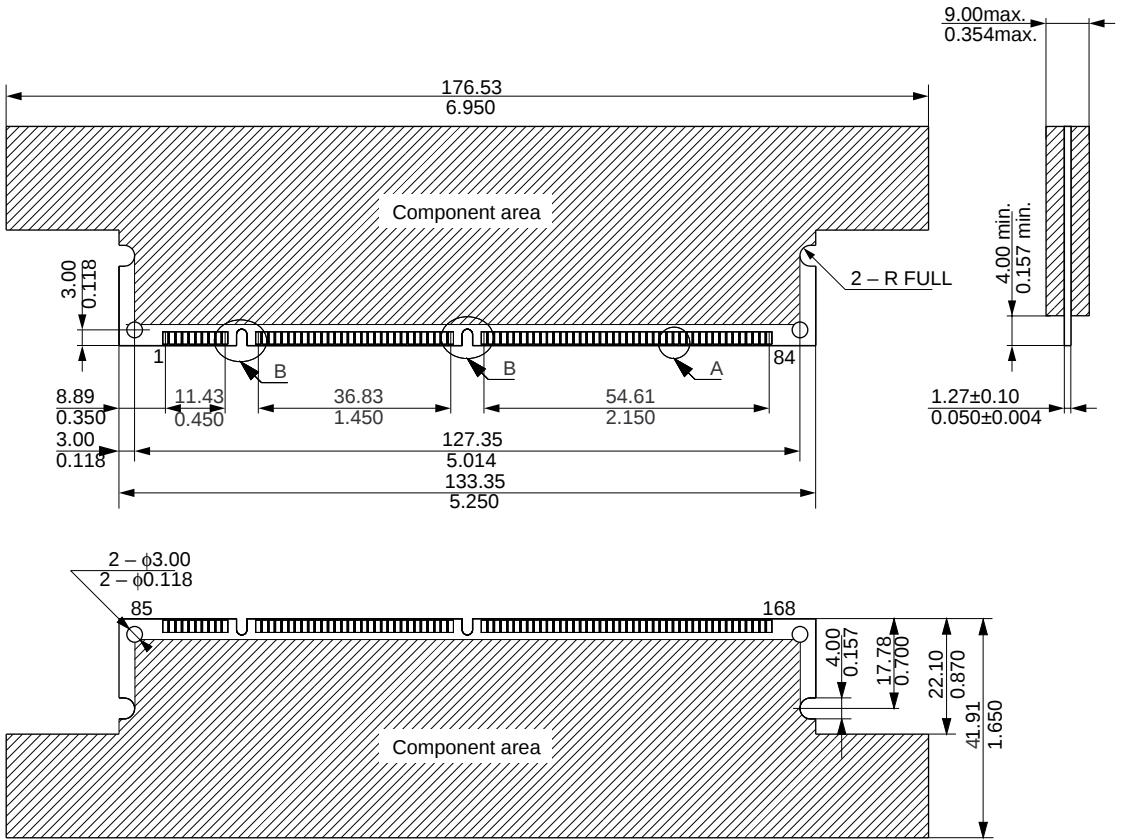


Detail A

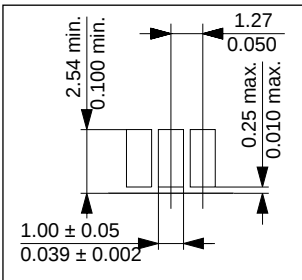


Detail B

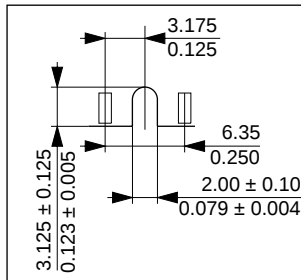




Detail A



Detail B



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0.0	Sep. 6, 1996	Initial issue		
